

Term	Plaintiff's Proposed Construction	Defendants' Proposed Construction	Court's Preliminary Construction
<p>“a second, thicker oxide layer” / “a gate oxide layer”</p> <p>U.S. Patent No. 8,035,112, Cls. 1, 6</p>	<p>“layer of oxide that is on the tops and sides of each gate and that is thicker than the layer of oxide below each gate”</p>	<p>“an oxidation layer formed, created, or grown by reacting the gate, thicker than the first oxide layer”</p>	<p>Plain-and-ordinary meaning</p>
<p>“double-implanted metal-oxide semiconductor field effect transistor”</p> <p>U.S. Patent No. 7,498,633, Cl. 9</p>	<p>The preamble is not limiting.</p> <p>In the alternative only, “double-implanted” is not limiting.¹</p>	<p>The preamble is limiting.</p>	<p>The preamble is limiting.</p>
<p>“less than about three micrometers”</p> <p>U.S. Patent No. 7,498,633, Cl. 9</p>	<p>Plain and ordinary meaning, no construction necessary.</p>	<p>Indefinite</p>	<p>Not indefinite. Plain-and-ordinary meaning.</p>

¹ ST notes that Purdue previously offered that “[i]n the alternative only, ‘metal-oxide semiconductor field-effect transistor is limiting.’”